

SEMITOP® 2

**IGBT** Module

SK25GB12T4

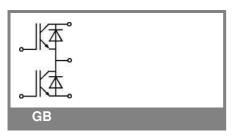
#### **Features**

- One screw mounting module
- Trench4 IGBT technology
- CAL4 technology FWD

## **Typical Applications\***

#### Remarks

• V<sub>CE,sat</sub> , V<sub>F</sub> = chip level value



<b>Absolute Maximum Ratings</b> $T_s = 25  ^{\circ}\text{C}$ , unless otherwise specified					
Symbol	Conditions			Values	Units
IGBT					
$V_{CES}$	T <sub>j</sub> = 25 °C			1200	V
I <sub>C</sub>	T <sub>j</sub> = 175 °C	T <sub>s</sub> = 25 °C		37	Α
		$T_s = 70  ^{\circ}C$		30	Α
I <sub>CRM</sub>	I <sub>CRM</sub> = 3 x I <sub>Cnom</sub>			75	Α
$V_{GES}$				± 20	V
t <sub>psc</sub>	$V_{CC}$ = 800 V; $V_{GE} \le 15$ V; $V_{CES} < 1200$ V	T <sub>j</sub> = 150 °C		10	μs
Inverse D	Diode				•
I <sub>F</sub>	T <sub>j</sub> = 175 °C	$T_s$ = 25 °C		30	Α
		$T_s = 70  ^{\circ}C$		25	Α
I <sub>FRM</sub>	I <sub>FRM</sub> = 3 x I <sub>Fnom</sub>			75	Α
I <sub>FSM</sub>	t <sub>p</sub> = 10 ms; half sine wave	T <sub>j</sub> = 150 °C		160	Α
Module					_
$I_{t(RMS)}$					Α
T <sub>vj</sub>				-40 <b>+</b> 175	°C
T <sub>stg</sub>				-40 <b>+</b> 125	°C
V <sub>isol</sub>	AC, 1 min.			2500	V

Characteristics $T_s =$			25 °C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units	
IGBT						•	
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_{C} = 0.85 \text{ mA}$		5	5,8	6,5	V	
I <sub>CES</sub>	V <sub>GE</sub> = 0 V, V <sub>CE</sub> = V <sub>CES</sub>	T <sub>j</sub> = 25 °C			1	mA	
		T <sub>j</sub> = 125 °C				mA	
I <sub>GES</sub>	V <sub>CE</sub> = 0 V, V <sub>GE</sub> = 20 V	T <sub>j</sub> = 25 °C			120	nA	
		$T_j = 125 ^{\circ}\text{C}$ $T_i = 25 ^{\circ}\text{C}$				nA	
V <sub>CE0</sub>		T <sub>j</sub> = 25 °C		1,1	1,3	V	
		T <sub>j</sub> = 150 °C		1	1,2	V	
r <sub>CE</sub>	V <sub>GE</sub> = 15 V	T <sub>j</sub> = 25°C		30		mΩ	
		$T_{j} = 150^{\circ}C$		50		mΩ	
V <sub>CE(sat)</sub>	I <sub>Cnom</sub> = 25 A, V <sub>GE</sub> = 15 V	T <sub>j</sub> = 25°C <sub>chiplev.</sub>		1,85	2,05	V	
		$T_j = 150^{\circ}C_{chiplev}$		2,25	2,45	V	
C <sub>ies</sub>				1,43		nF	
C <sub>oes</sub>	$V_{CE} = 25, V_{GE} = 0 V$	f = 1 MHz		0,115		nF	
C <sub>res</sub>				0,085		nF	
$Q_G$	V <sub>GE</sub> =-7V+15V			137,5		nC	
t <sub>d(on)</sub>				22		ns	
t <sub>r</sub>	$R_{Gon} = 19 \Omega$	V <sub>CC</sub> = 600V		19,5		ns	
E <sub>on</sub>	di/dt = 2825 A/μs	I <sub>C</sub> = 25A		2,27		mJ	
<sup>t</sup> d(off)	$R_{Goff} = 19 \Omega$	T <sub>j</sub> = 150 °C		288		ns	
t <sub>f</sub>	di/dt = 2825 A/µs	V <sub>GE</sub> = -7/+15V		77,5		ns	
E <sub>off</sub>				2,7		mJ	
$R_{th(j-s)}$	per IGBT			1,31		K/W	



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### Typical Applications\*

#### Remarks

V<sub>CF sat</sub> , V<sub>F</sub> = chip level value

Characteristics								
Symbol	Conditions		min.	typ.	max.	Units		
Inverse Diode								
$V_F = V_{EC}$	$I_{Fnom}$ = 25 A; $V_{GE}$ = 0 V	$T_j = 25  ^{\circ}C_{\text{chiplev.}}$		2,4	2,62	V		
		$T_j$ = 150 °C <sub>chiplev</sub> .		2,45	2,8	V		
V <sub>F0</sub>		T <sub>j</sub> = 25 °C		1,3	1,5	V		
		T <sub>j</sub> = 150 °C		0,9	1,1	V		
r <sub>F</sub>		T <sub>j</sub> = 25 °C		44	45	mΩ		
		T <sub>j</sub> = 150 °C		62	68	mΩ		
I <sub>RRM</sub>	I <sub>F</sub> = 25 A	T <sub>i</sub> = 150 °C		31,5		Α		
$Q_{rr}$	di/dt = 2825 A/µs	•		1,15		μC		
E <sub>rr</sub>	V <sub>CC</sub> = 600V			1,28		mJ		
$R_{th(j-s)D}$	per diode			1,91		K/W		
M <sub>s</sub>	to heat sink		2,25		2,5	Nm		
w				30		g		

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

#### \*IMPORTANT INFORMATION AND WARNINGS

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